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Kind regards,

Team Nexperia

PDTA124E series

PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

Rev. 8 — 25 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN	Package	
	NXP	JEITA	JEDEC	complement	configuration	
PDTA124EE	SOT416	SC-75	-	PDTC124EE	ultra small	
PDTA124EM	SOT883	SC-101	-	PDTC124EM	leadless ultra small	
PDTA124ET	SOT23	-	TO-236AB	PDTC124ET	small	
PDTA124EU	SOT323	SC-70	-	PDTC124EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital applications in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		15.4	22	28.6	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2. Pinning information

Table 3. **Pinning** Simplified outline **Graphic symbol** Pin Description SOT23; SOT323; SOT416 1 input (base) 3 GND (emitter) 2 3 output (collector) 006aaa144 sym003 **SOT883** 1 input (base) 2 GND (emitter) output (collector) Transparent

3. Ordering information

Table 4. Ordering information

Type number	Package						
	Name	Description	Version				
PDTA124EE	SC-75	plastic surface-mounted package; 3 leads	SOT416				
PDTA124EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883				
PDTA124ET	-	plastic surface-mounted package; 3 leads	SOT23				
PDTA124EU	SC-70	plastic surface-mounted package; 3 leads	SOT323				

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PDTA124EE	05
PDTA124EM	DH
PDTA124ET	*05
PDTA124EU	*05

[1] * = placeholder for manufacturing site code

sym003

5. Limiting values

Table 6. Limiting values

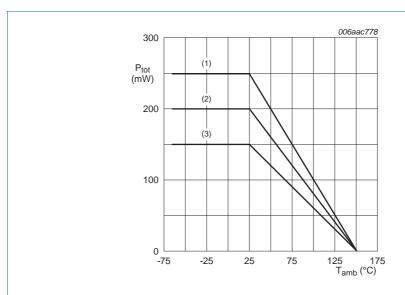
In accordance with the Absolute Maximum Rating System (IEC 60134).

			<u> </u>		
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-10	V
V_{I}	input voltage				
	positive		-	+10	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PDTA124EE (SOT416)		[1][2]	150	mW
	PDTA124EM (SOT883)		[2][3]	250	mW
	PDTA124ET (SOT23)		<u>[1]</u> -	250	mW
	PDTA124EU (SOT323)		[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- (1) SOT23; FR4 PCB, standard footprint SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

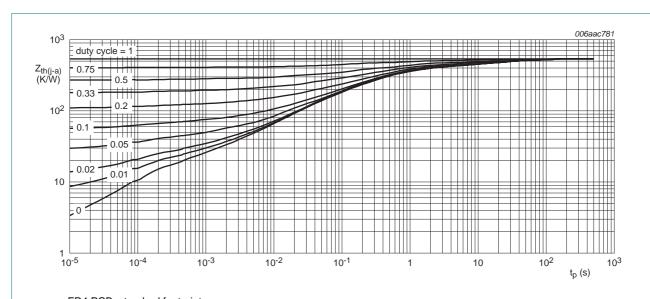
Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

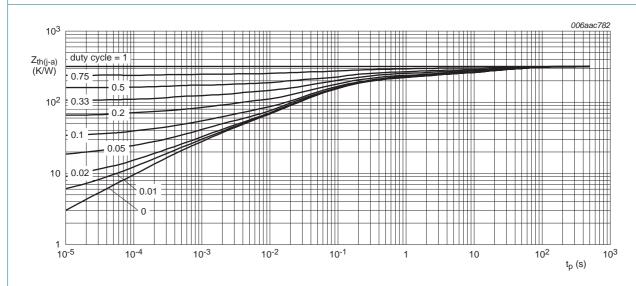
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA124EE (SOT416)		[1][2]	-	830	K/W
	PDTA124EM (SOT883)		[2][3]	-	500	K/W
	PDTA124ET (SOT23)		[1] _	-	500	K/W
	PDTA124EU (SOT323)		<u>[1]</u> -	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA124EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA124EM (SOT883); typical values

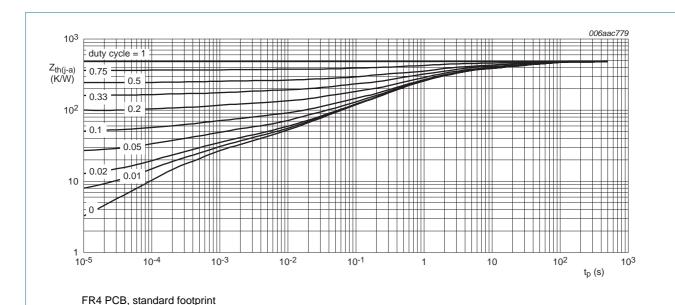


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA124ET (SOT23); typical values

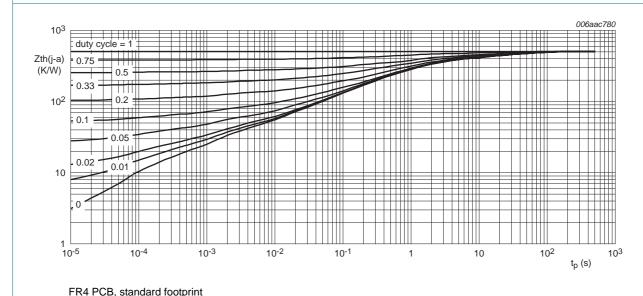


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA124EU (SOT323); typical values

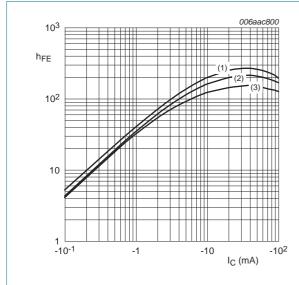
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-100	nA
	cut-off current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-180	μΑ
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	60	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -5 \text{ mA}$	-2.5	-1.7	-	V
R1	bias resistor 1 (input)		15.4	22	28.6	$k\Omega$
R2/R1	bias resistor ratio		8.0	1	1.2	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA}; $ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

[1] Characteristics of built-in transistor



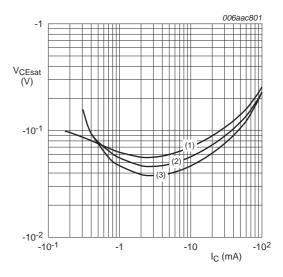


⁽¹⁾ $T_{amb} = 100 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

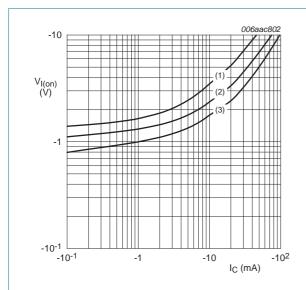
(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

PDTA124E_SER

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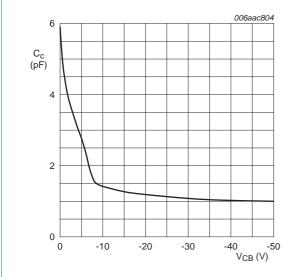
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

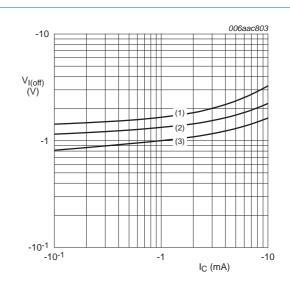
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



 $f = 1 \text{ MHz}; T_{amb} = 25 \text{ }^{\circ}\text{C}$

Fig 10. Collector capacitance as a function of collector-base voltage; typical values



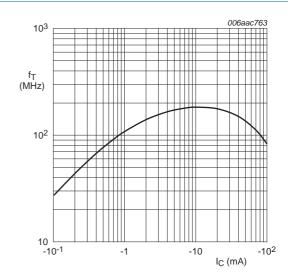
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}; T_{amb} = 25 \text{ }^{\circ}\text{C}$$

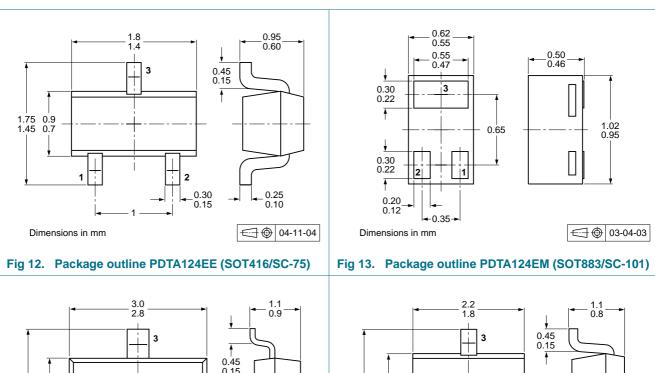
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

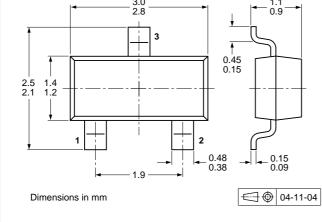
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline







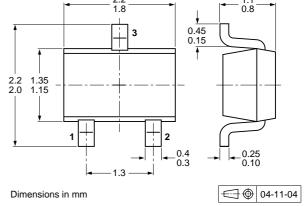


Fig 15. Package outline PDTA124EU (SOT323/SC-70)

10. Packing information

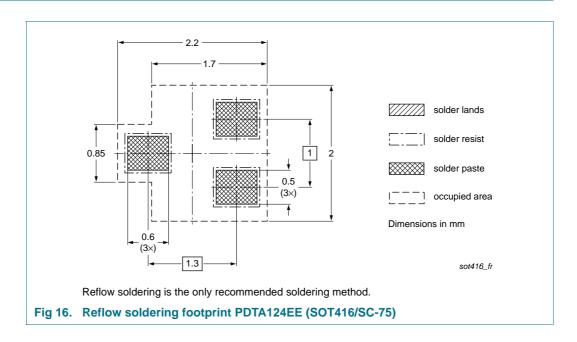
Table 9. Packing methods

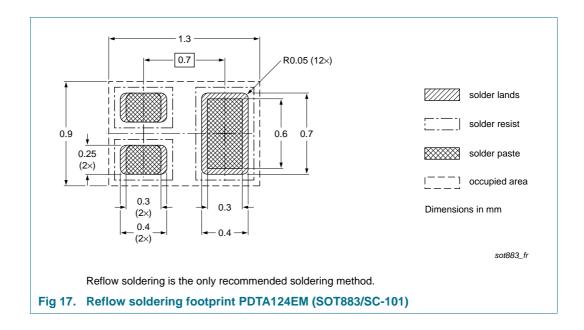
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

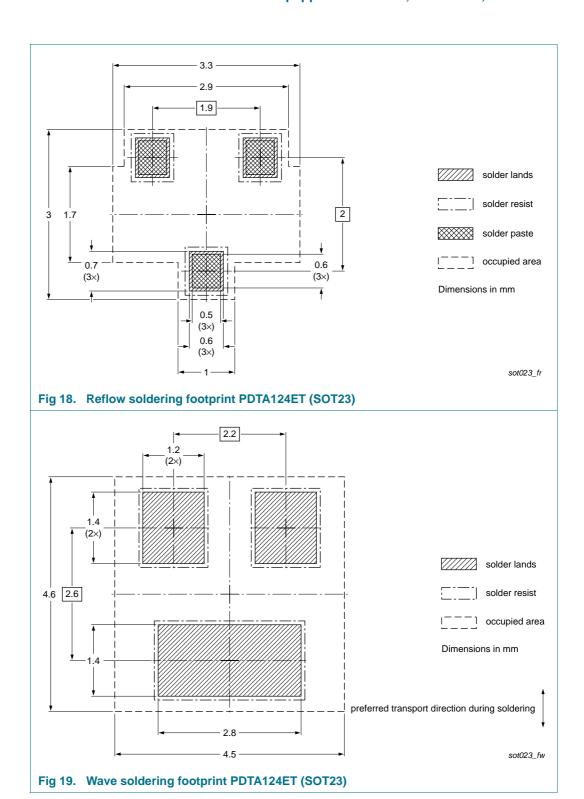
Type number	Package	Description	Packing o	cking quantity	
			3000	5000	10000
PDTA124EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135
PDTA124EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-	-315
PDTA124ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
PDTA124EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135

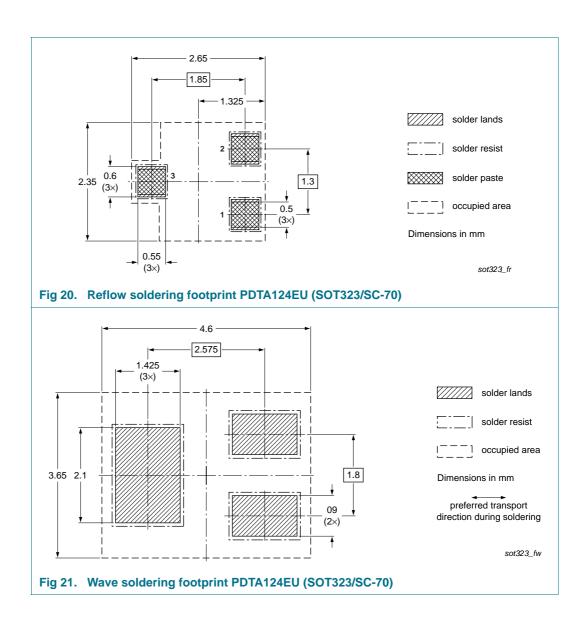
^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering









12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PDTA124E_SER v.8	20111125	Product data sheet	-	PDTA124E_SERIES v.7			
Modifications:		of this document has been NXP Semiconductors.	redesigned to comply w	ith the new identity			
	 Legal texts h 	nave been adapted to the n	new company name whe	re appropriate.			
	 Type numbe 	rs PDTA124EEF, PDTA124	4EK and PDTA124ES re	emoved.			
	 Section 1 "Product profile": updated 						
	 Section 3 "O 	 Section 3 "Ordering information": added 					
	Section 4 "Marking": updated						
	• Figure 1 to 11: added						
	Section 6 "Tl	hermal characteristics": up	dated				
	 <u>Table 8 "Characteristics"</u>: V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "Te	est information": added					
	Section 9 "Page 1.5"	ackage outline": supersede	ed by minimized packag	e outline drawings			
	Section 10 "I	Packing information": adde	ed				
	Section 11 "Soldering": added						
Section 13 "Legal information": updated							
PDTA124E_SERIES v.7	20040805	Product data sheet	-	PDTA124E_SERIES v.6			
PDTA124E_SERIES v.6	20030414	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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PDTA124E_SER

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PDTA124E series

PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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PDTA124E series

PNP resistor-equipped transistors; R1 = 22 k Ω , R2 = 22 k Ω

15. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data
2	Pinning information
3	Ordering information
4	Marking
5	Limiting values
6	Thermal characteristics
7	Characteristics
8	Test information
8.1	Quality information
9	Package outline
10	Packing information 10
11	Soldering 10
12	Revision history
13	Legal information1
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks16
14	Contact information
15	Contents 17

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